

Super-Junction Power Mosfet

1. Product Information

Features

- Super Junction technology
- Low FOM $R_{DS(ON)} \times Q_G$
- Lead free product is acquired

Applications

- Charger
- Power Supply
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

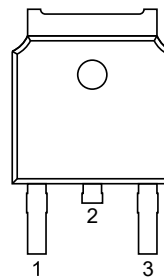
Quick reference

- $V_{DS} \geq 650 \text{ V}$
- $I_D \leq 8 \text{ A}$
- $R_{DS(ON)} \leq 550 \text{ m}\Omega @ V_{GS}=10 \text{ V}$ (Type 420 m Ω)

Pin Description

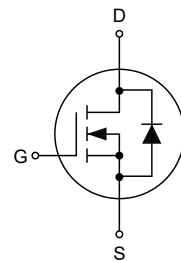
Pin	Description
1	Gate(G)
2	Drain(D)
3	Source(S)

Simplified Outline



Top View
TO-252

Symbol



Package Marking and Ordering Information

Part number	Marking	Package	Packaging	Quantity	Reel size	Tape width
KJC65R550K	KJC65R550K	TO-252-3L	☒ Tape & Reel	2500 PCS	13"	16 mm
			☐ Tube	N/A	N/A	N/A

2. Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Continuous Drain Current (T _C =25°C)	8	A
	Continuous Drain Current (T _C =100°C)	5	A
I_{DM}	Pulsed Drain Current	32	A
E_{AS}	Single Pulsed Avalanche Energy	66	mJ
I_{AR}	Avalanche Current	2.1	A
P_D	Power Dissipation	73	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance, Junction-Ambient	140	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-Case	1.7	°C/W

3. Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Type	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _D =250 μA	650	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =650 V, V _{GS} =0 V	-	-	1	μA
		V _{DS} =650 V, T _C =150°C	-	1	-	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±30 V, V _{DS} =0 V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250 μA	3	-	4	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10 V, I _D =4 A	-	420	550	mΩ
R _g	Gate resistance	f=1 MHz	-	15	-	Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =100 V, V _{GS} =0 V, f=1 MHz	-	490	-	pF
C _{oss}	Output Capacitance		-	25	-	pF
C _{rss}	Reverse Transfer Capacitance		-	0.65	-	pF
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =400 V, I _D =4 A, R _G =27 Ω, V _{GS} =10 V	-	15	-	ns
t _r	Turn-on Rise Time		-	17.5	-	ns
t _{d(off)}	Turn-off Delay Time		-	82	-	ns
t _f	Turn-off Fall Time		-	16	-	ns
Q _g	Total Gate Charge	V _{DS} =480 V, I _D =4 A, V _{GS} =10 V	-	16	-	nC
Q _{gs}	Gate-Source Charge		-	3.5	-	nC
Q _{gd}	Gate-Drain Charge		-	7	-	nC
Source-Drain Diode Characteristics						
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} =0 V, I _F =3.5 A	-	0.85	1.1	V
Q _{rr}	Reverse Recovery Time	V _{DS} =400 V, I _{SD} =4 A, di/dt=100 A/μs	-	1.8	-	μC
T _{rr}	Reverse Recovery Charge		-	210	-	ns

4. Electrical Characteristics

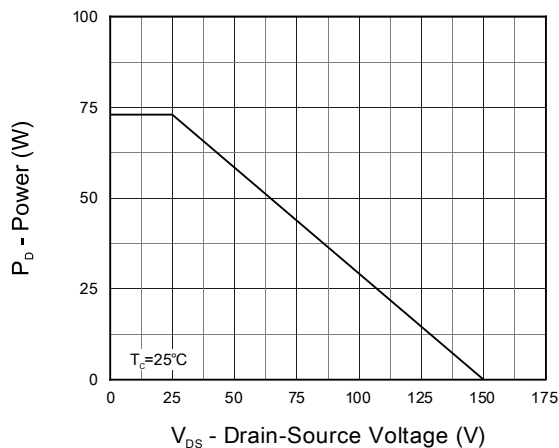


Fig 1. Power Characteristics

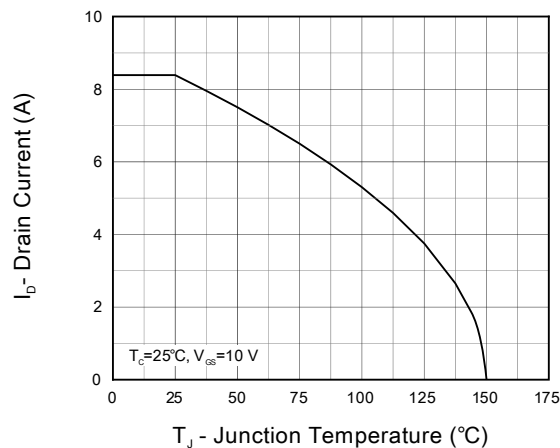


Fig 2. Current Capability

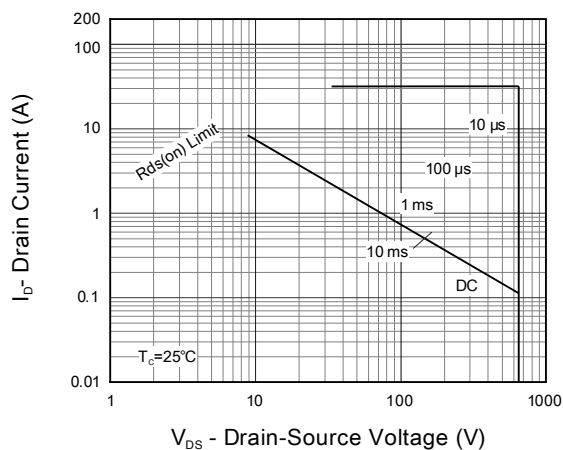


Fig 3. Safe Operation Area

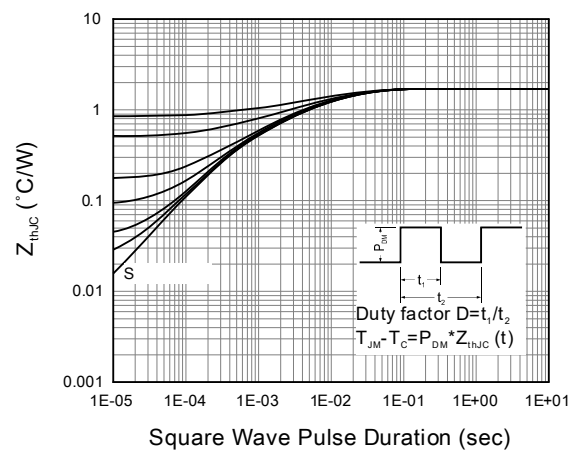


Fig 4. Transient Thermal Impedance

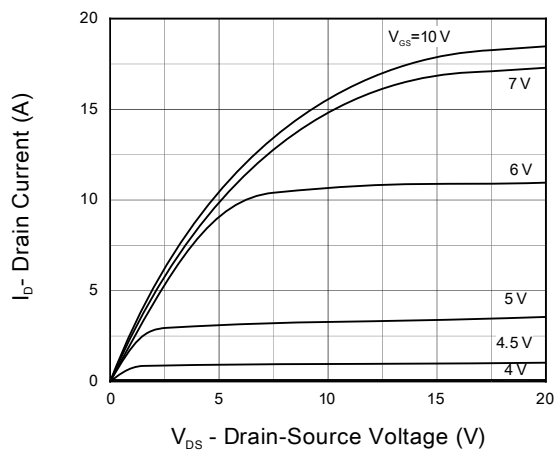


Fig 5. Output Characteristics
 $T_J=25^\circ\text{C}$

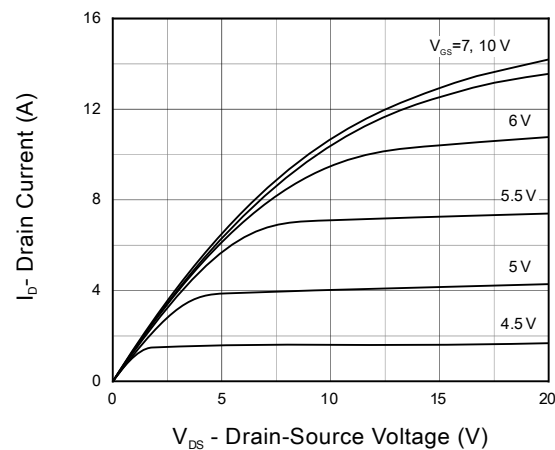


Fig 6. Output Characteristics
 $T_J=150^\circ\text{C}$

5. Electrical Characteristics (cont.)

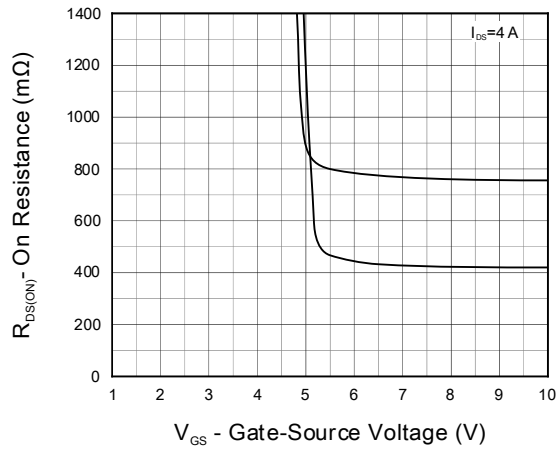


Fig 7. Transfer Characteristics

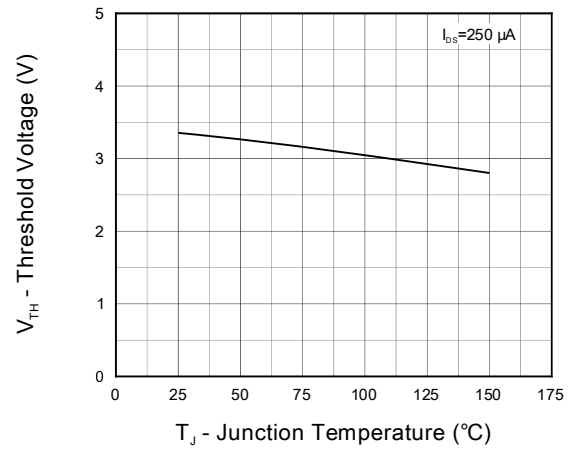


Fig 8. Normalized Threshold Voltage

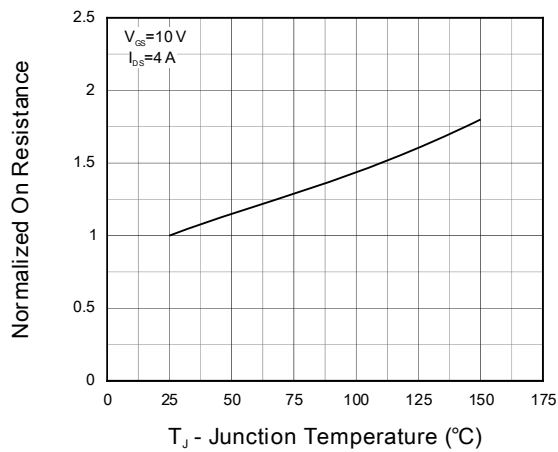


Fig 9. Normalized On Resistance

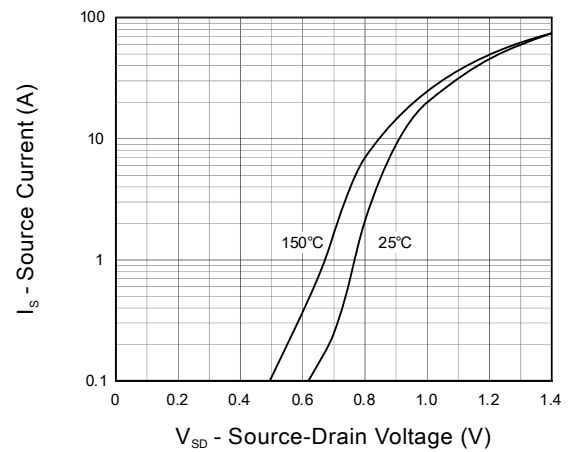


Fig 10. Diode Forward Current

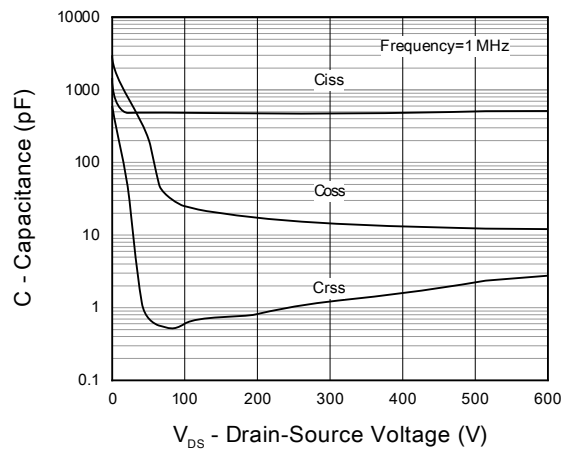


Fig 11. Capacitance

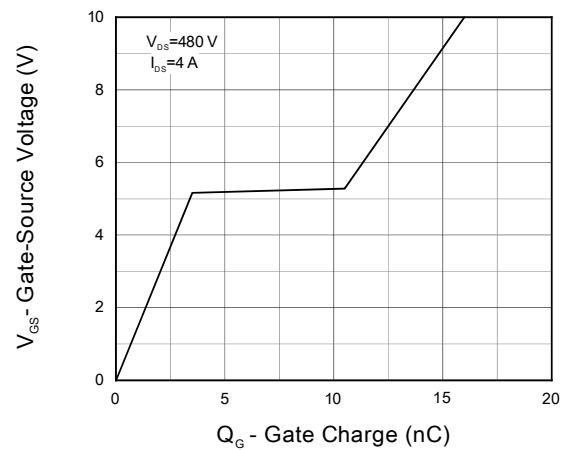
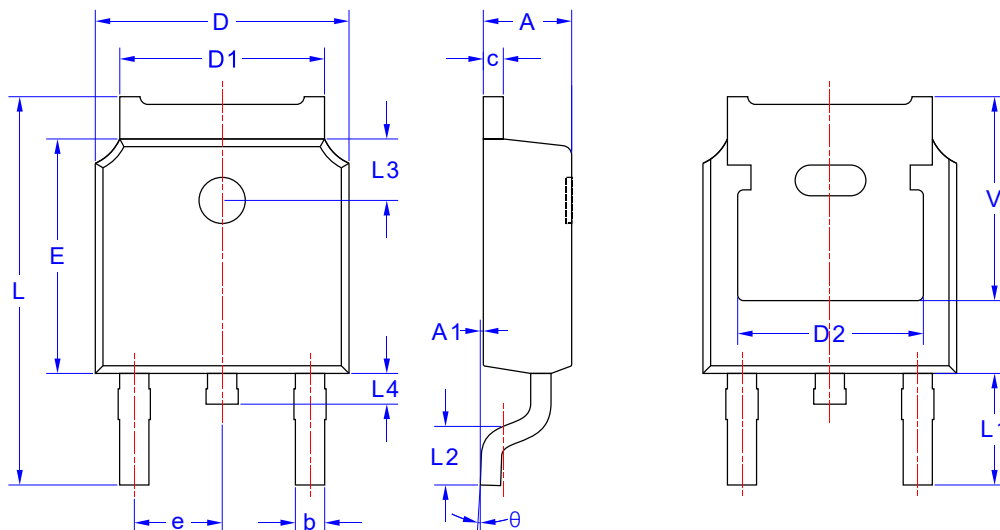


Fig 12. Gate Charge

5. Package Mechanical Data

TO-252 Package



Symbol	Dimensions in Millimeters	
	MIN	MAX
A	2.200	2.400
A1	0	0.127
b	0.660	0.860
c	0.460	0.580
D	6.500	6.700
D1	5.100	5.460
D2	4.830 REF.	
E	6.000	6.200
e	2.186	2.386
L	9.800	10.400
L1	2.900 REF.	
L2	1.400	1.700
L3	1.800 REF.	
L4	0.600	1.000
θ	0°	8°
V	5.600 REF.	